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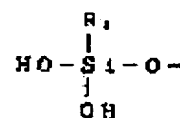
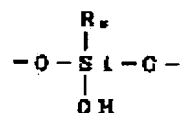
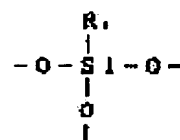
JP

(54) RESIST MATERIAL, ITS MANUFACTURE, AND PATTERN FORMING METHOD USING SAME

(57)Abstract:

PURPOSE: To obtain the alkali-developable type resist material high in glass transition point, superior in O₂ RIE resistance, and usable against energy rays in a wide range by composing the resist with a specified polysiloxane and an acid generating agent.

CONSTITUTION: The polysiloxane to be used has structural units each represented by formulae I-III and each unit combines with each other to form a siloxane bond and to form the siloxane, and the acid generating agent is used together with the polysiloxane. In formulae I-III, each of R₁-R₃ is an organic residue, and one or all of them has an oxirane ring. Such a resist material may contain an organic polymer having hydroxyl groups or an epoxy compound. It is preferred that a part of R₁-R₃ is a 2-(3,4-epoxycyclohexyl)-ethyl group and the other is a phenyl group and the acid generating agent is diphenyl-4-thiophenoxyphenylsulfoniumhexafluorophosphate.



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